

ABSTRACT

**SUBSTRATE FOR A TEMPERATURE-COMPENSATED SURFACE ACOUSTIC WAVE
DEVICE OR BULK ACOUSTIC WAVE DEVICE**

The invention relates to a substrate (1) for a surface acoustic wave device or bulk acoustic wave device, comprising a support substrate (11) and an piezoelectric layer (10) on said support substrate, characterised in that the support substrate (11) comprises a semiconductor layer (111) on a stiffening substrate (110) having a coefficient of thermal expansion that is closer to the coefficient of thermal expansion of the material of the piezoelectric layer (10) than that of silicon, the semiconductor layer (111) being arranged between the piezoelectric layer (10) and the stiffening substrate (110).

Figure 3